

HiPerFRED

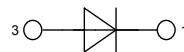
High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 Single Diode

V_{RRM} = 600 V
I_{FAV} = 6 A
t_{rr} = 20 ns

Part number

DSEP6-06AS

Marking on Product: 6P060AS



Backside: cathode

Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm}-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

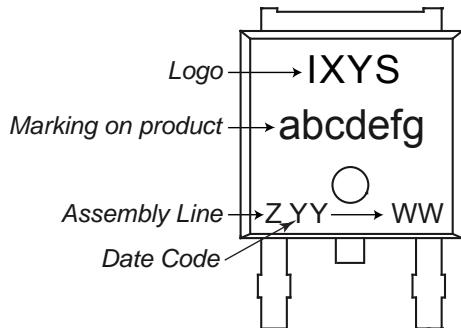
Package:

- Housing: TO-252 (DPak)
- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

Ratings								
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RRM}	max. repetitive reverse voltage		T _{VJ} = 25 °C			600	V	
I _R	reverse current	V _R = 600 V	T _{VJ} = 25 °C			50	µA	
		V _R = 600 V	T _{VJ} = 150 °C			0.2	mA	
V _F	forward voltage	I _F = 6 A	T _{VJ} = 25 °C			2.03	V	
		I _F = 12 A				2.22	V	
		I _F = 6 A	T _{VJ} = 150 °C			1.34	V	
		I _F = 12 A				1.55	V	
I _{FAV}	average forward current	rectangular	d = 0.5	T _C = 150 °C			6	A
V _{F0}	threshold voltage	slope resistance } for power loss calculation only		T _{VJ} = 175 °C			1.00	V
r _F	slope resistance						34	mΩ
R _{thJC}	thermal resistance junction to case					2.80	K/W	
T _{VJ}	virtual junction temperature			-55		175	°C	
P _{tot}	total power dissipation		T _C = 25 °C			55	W	
I _{FSM}	max. forward surge current	t = 10 ms (50 Hz), sine	T _{VJ} = 45 °C			40	A	
I _{RM}	max. reverse recovery current		T _{VJ} = 25 °C			3	A	
		I _F = 6 A; V _R = 300 V	T _{VJ} = 100 °C			5	A	
t _{rr}	reverse recovery time	-di _F /dt = 200 A/µs	T _{VJ} = 25 °C			20	ns	
			T _{VJ} = 100 °C			80	ns	
C _J	junction capacitance	V _R = 400 V; f = 1 MHz	T _{VJ} = 25 °C			5	pF	

Symbol	Definition	Conditions	Ratings			
			min.	typ.	max.	
I_{RMS}	RMS current	per terminal			20	A
R_{thCH}	thermal resistance case to heatsink			0.50		K/W
T_{stg}	storage temperature		-55		150	°C
Weight				0.3		g
F_c	mounting force with clip		20		60	N

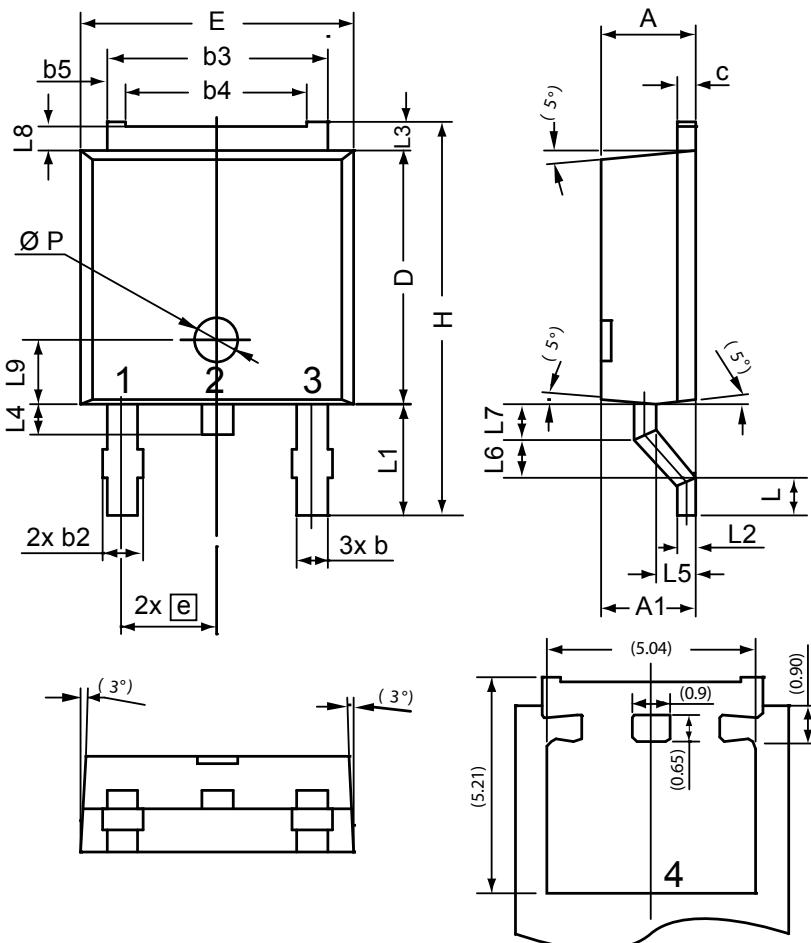
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEP6-06AS	6P060AS	Tape & Reel	2500	509806

Similar Part	Package	Voltage Class
DSEP6-06BS	TO-252AA (DPak)	600

Outlines TO-252 (DPak)



Dim.	Millimeters		Inches	
	min	max	min	max
A	2.20	2.40	0.087	0.094
A1	2.10	2.50	0.083	0.098
b	0.66	0.86	0.026	0.034
b2	-	0.96	-	0.038
b3	5.04	5.64	0.198	0.222
b4	4.34	BSC	0.171	BSC
b5	0.50	BSC	0.020	BSC
c	0.40	0.60	0.016	0.024
D	5.90	6.30	0.232	0.248
E	6.40	6.80	0.252	0.268
e	2.10	2.50	0.083	0.098
H	9.20	9.80	0.362	0.386
L	0.55	1.02	0.022	0.040
L1	2.50	2.90	0.098	0.114
L2	0.40	0.60	0.016	0.024
L3	0.50	0.90	0.020	0.035
L4	0.60	1.00	0.024	0.039
L5	0.82	1.22	0.032	0.048
L6	0.79	0.99	0.031	0.039
L7	0.81	1.01	0.032	0.040
L8	0.40	0.80	0.016	0.031
L9	1.50	BSC	0.059	BSC
Ø P	1.00	BSC	0.039	BSC

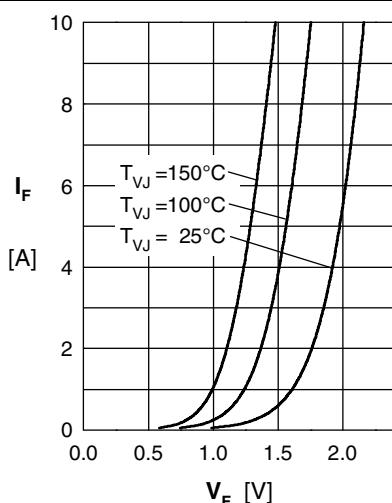
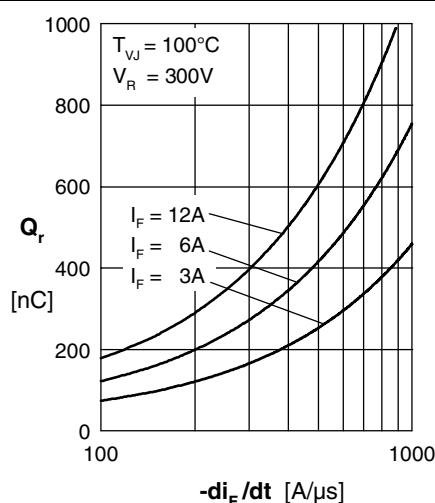
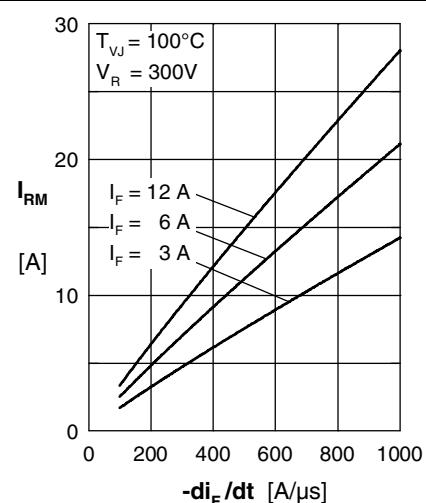
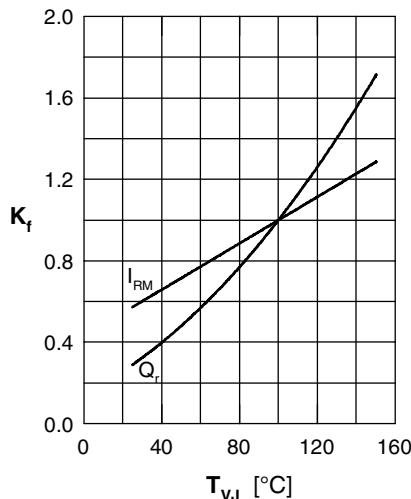
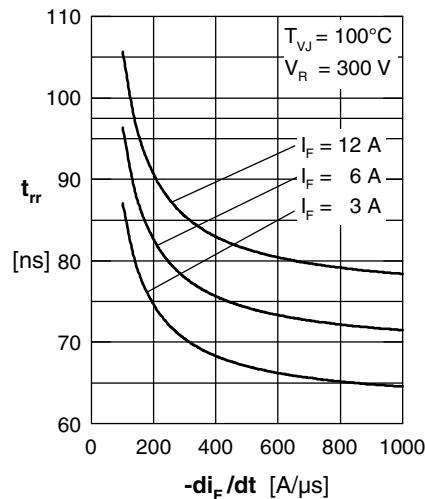
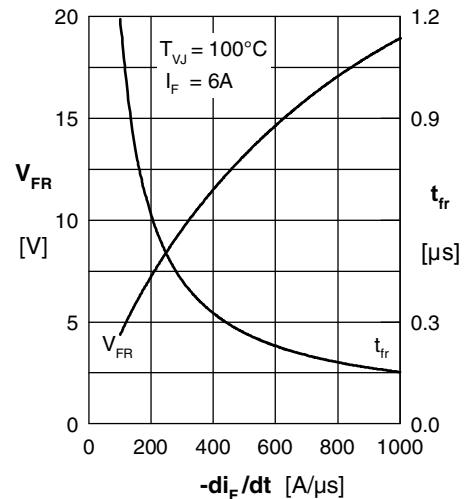
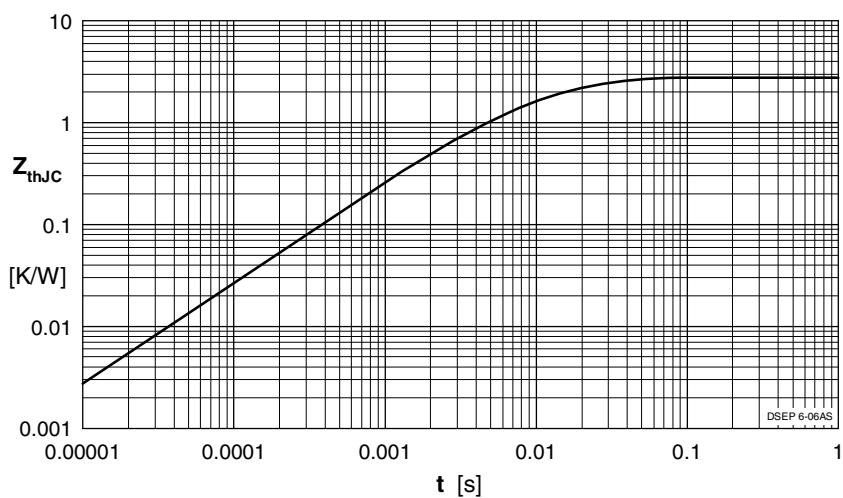
Fig. 1 Forward current I_F vs. V_F Fig. 2 Reverse recovery charge Q_r versus $-di_F/dt$ Fig. 3 Peak reverse current I_{RM} versus $-di_F/dt$ Fig. 4 Dynamic parameters Q_r , I_{RM} versus T_{VJ} Fig. 5 Recovery time t_{rr} versus $-di_F/dt$ Fig. 6 Peak forward voltage V_{FR} and t_{fr} versus di_F/dt 

Fig. 7 Transient thermal resistance junction to case